

isc Silicon NPN Power Transistor

2SC2987A

DESCRIPTION

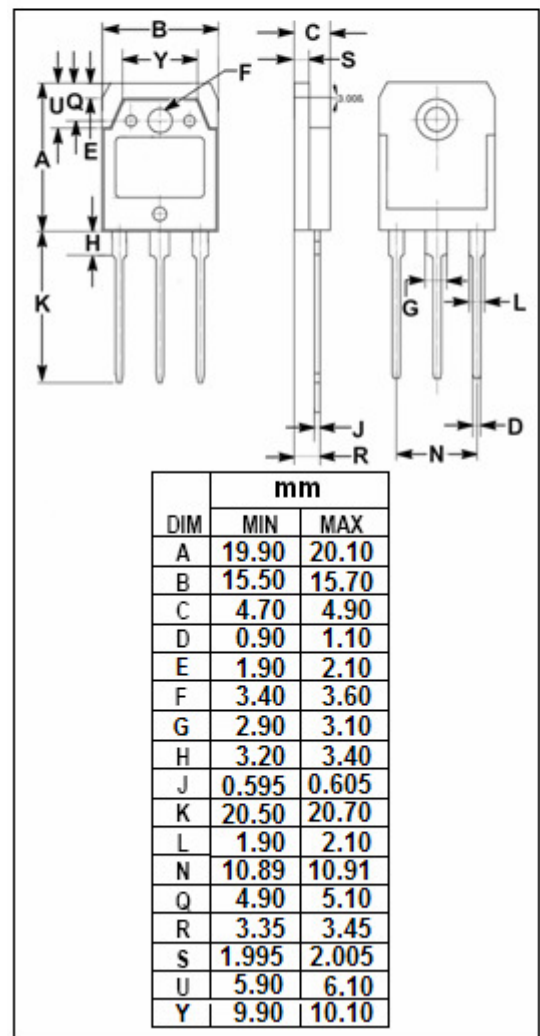
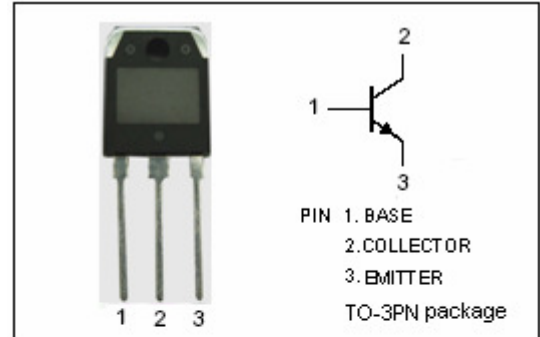
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 160V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SA1227A

APPLICATIONS

- For audio frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	12	A
I_{CP}	Collector Current-Pulse	20	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	120	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SC2987A****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 5.0A; I_B= 0.5A$			1.5	V
$V_{BE(sat)}$	Base -Emitter Saturation Voltage	$I_C= 5.0A; I_B= 0.5A$			2.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB}= 140V; I_E= 0$			50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}= 3V; I_C= 0$			50	μA
h_{FE-1}	DC Current Gain	$I_C= 2A; V_{CE}= 5V$	60		320	
h_{FE-2}	DC Current Gain	$I_C= 5A; V_{CE}= 5V$	40			
C_{OB}	Output Capacitance	$I_E= 0; V_{CB}= 10V; f_{test}= 1.0MHz$		190		pF
f_T	Current-Gain—Bandwidth Product	$I_C= 1A; V_{CE}= 5V$		50		MHz

◆ **h_{FE-1} Classifications**

R	Q	P
60-120	100-200	160-320